ECE-255 Exam II March/3/2010

B. L'air	(Please print clearly)	Student ID:
Name:		

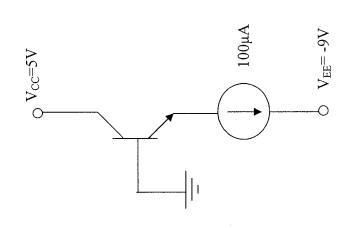
INSTRUCTIONS

- This is a closed book, closed notes exam.
- multiple choice problems and marked answers in the test booklet will not be Work on Carefully mark your multiple choice answers on the scantron form. graded. Nothing is to be on the seat beside you.
- When the exam ends, all writing is to stop. This is not negotiable. No writing while turning in the exam/scantron or risk an F in the exam.
- All students are expected to abide by the customary ethical standards of the university, i.e., your answers must reflect only your own knowledge and reasoning ability. As a reminder, at the very minimum, cheating will result in a zero on the exam and possibly an F in the course.
- of the exam is grounds for immediate ejection from the exam site and loss of all Communicating with any of your classmates, in any language, by any means, for any reason, at any time between the official start of the exam and the official end credit for this exercise.

- 1) In a bipolar transistor operating in the forward active region,

- BE and BC junctions are both reverse biased
 BE and BC junctions are both reverse biased
 BE junction is forward biased and BC junction is reverse biased
 BE junction is reverse biased and BC junction is forward biased
 BE junction is forward biased and CE junction is forward biased
 BE junction is reverse biased and CE junction is forward biased

2) For the bipolar circuit shown below, $V_{\rm CE}{=}7$ $\beta{=}100,\,I_s{=}10^{-1}{^4}A,$ and $V_T{=}25{\rm mV}$



(1) 14V (2) 5.575V (3) 0.7V (5) 4.425 (6) None of the above

(4) 5V

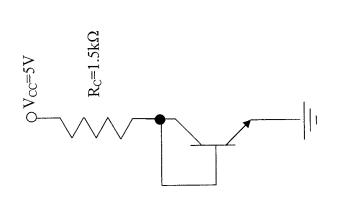
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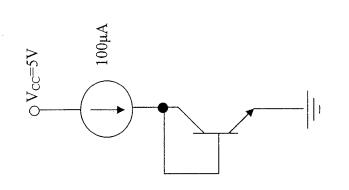
0.575/25.57 11)

3) For the bipolar circuit shown below, I_C ? β =100, $V_{BE}(on)$ =0.7



- (1) 3.13mA (2) 2.8 (5) 1.43mA (6) NG
- (2) 2.84 mA (3) 3.8 mA (6) None of the above
- (4) 3.33mA
- (| 10 11
- 2.84mA 11

4) For the diode connected bipolar transistor shown below, $V_{\rm BE} \!\!=\!\! ?$ $\beta \!\!=\!\! 100,\,I_s \!\!=\!\! 10^{\text{-}14} A,$ and $V_T \!\!=\!\! 25mV$

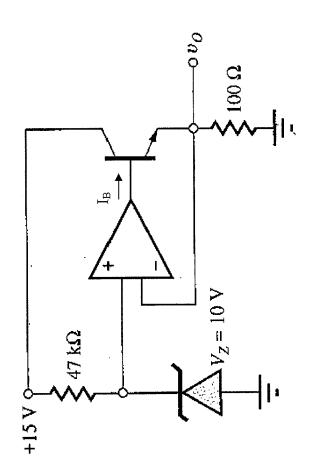


(1) 5V (2) 0.7V (3) 0V (5) 0.575V (6) None of the above

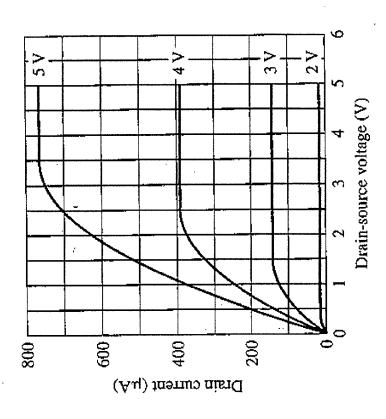
(4) - 0.575V

- ag LA () 001 U 000
- 520.0 ()

5) For the circuit shown below, what is I_B ? Assume OpAmp is ideal, β =60, and R_Z =0



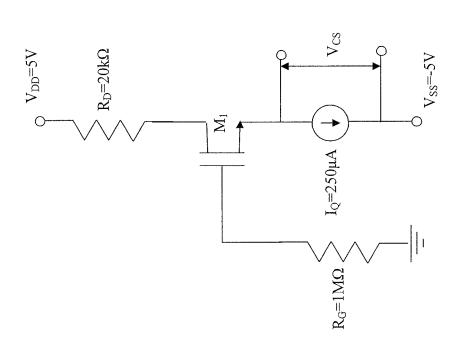
6) What is the value of VTN for the transistor whose ip-vps characteristic is given below?





7) For the MOS circuit shown below, what is the voltage drop across the current source, $V_{CS} = ?$

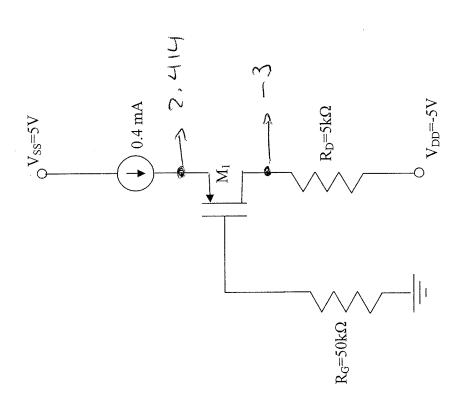
$$V_{TN}=1V$$
, $K'_N=80 \mu A/V^2$, $(W/L)=3$



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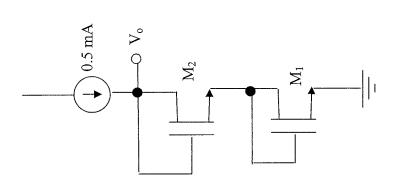
8) For the MOS circuit shown below, V_{DS} =?

$$V_{TP} = \text{-}0.8 \mathrm{V}$$
 , $K_P \!\!=\!\! 400~\mu A/V^2$



$$(1)$$
 -5.2V (2) -0.6V (3) 0V (4) 2.5V (5) 2.4V (6) None of the above

9) Find the output voltage (V_o) for the circuit shown below, V_{TN} =0.75V, K_N =100 μ A/V², (W/L)₁=10/1, (W/L)₂=20/1



(1) 3.2V (4) 2.5V

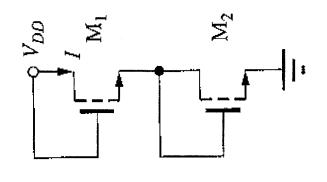
(2) 1.5V (5) it is open circuit

(3) 0V (6) None of the above

$$= V_{GS1} + V_{GS2}$$

$$= V_{GS2} + V_$$

 V_{DD} =10V and both transistors have W/L=10/1, V_{TN} =0.75V, and K_N =100 μ A/V² 10) Find the current I in the circuit below



- (2) 0mA since gates are tied to drains (transistors are off)
 (4) 0.9mA
 (6) None of the above (3) 9.03mA 1) 18mA 5) 42mA
- Galem) 01 X 1.0 1 () 11 Jame